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Robert Bosch, Stuttgart

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Revised Claims

What is claimed is:

1. A method of manufacturing semiconductor components, depressions being introduced into a wafer of a first conductivity type; in a further step, both sides of the wafer being coated with doping atoms, and a diffusion process being carried out; and, in further step, the wafer being diced into individual chips, so that, in its internal area (70), each chip has at least one depression (60), wherein the depressions are sawed.
2. The method according to Claim 1, wherein the depressions are formed as pits having a rectangular cross section.
3. The method according to Claim 1 or 2, wherein metal layers are applied to both sides of the wafer before the wafer is diced.
4. The method according to one of the preceding claims, wherein the wafer is diced in areas (40) of the wafer where no depressions have been introduced.
5. The method according to one of the preceding claims, wherein a dopant of a second conductivity type is used in covering the top side.
6. The method according to one of the preceding claims, wherein a dopant of the first type of conductivity is used in covering the bottom side.
7. The method according to one of the preceding claims,

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